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Inclosure Material:

Metal all transistor

Overall Length:

0.970 inches all transistor and 1.218 inches all transistor

Function For Which Designed:

Amplifier

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Threaded stud all transistor

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

0.424 inches all transistor and 0.437 inches all transistor

Thread Size:

0.190 inches all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

80.0 collector to base voltage/static/emitter open all transistor and 15.0 emitter to base voltage, static, collector open all transistor and 60.0 breakdown voltage, collector to emitter, sustained all transistor

Current Rating Per Characteristic:

10.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

30.0 watts large-signal input power, common-emitter all transistor

Maximum Operating Temperature Per Measurement Point:

200.0 degrees celsius ambient air all transistor

Special Features:

Subject transistor set is compound connected

Thread Series Designator:

Unf all transistor

Terminal Type And Quantity:

3 tab, solder lug all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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